

## POWER SCHOTTKY RECTIFIER

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	10 A
$V_{RRM}$	45 V
$V_F (max)$	0.57 V

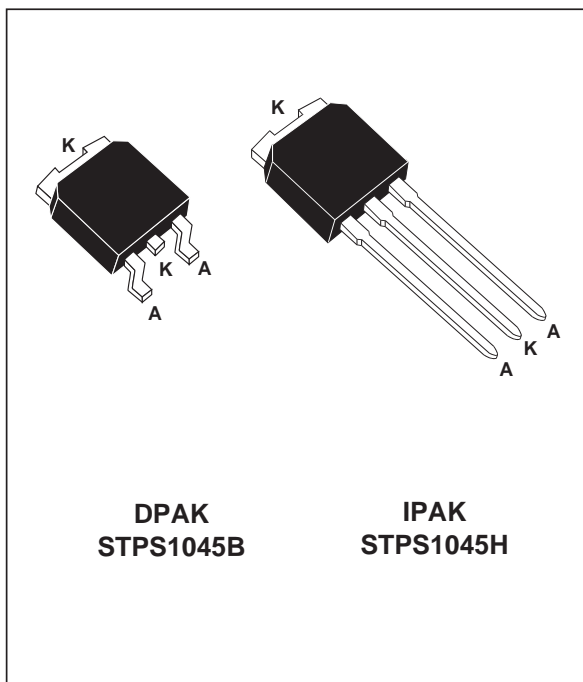
### FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD DROP VOLTAGE
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY
- AVALANCHE CAPABILITY SPECIFIED

### DESCRIPTION

High voltage Schottky rectifier suited for Switch Mode Power Supplies and other Power Converters.

Packaged in DPAK and IPAK, these devices are intended for use in high frequency circuitries where low switching losses are required.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		45	V
$I_{F(RMS)}$ / pin	RMS forward current / pin		7	A
$I_{F(AV)}$	Average forward current	$T_c = 150^{\circ}\text{C}$ $d = 0.5$	10	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	75	A
$I_{RRM}$	Repetitive peak reverse current	$t_p = 2 \mu\text{s}$ $F = 1\text{KHz}$	1	A
$P_{ARM}$	Repetitive peak avalanche power	$t_p = 1\mu\text{s}$ $T_j = 25^{\circ}\text{C}$	4000	W
$T_{stg}$	Storage temperature range		- 65 to + 175	$^{\circ}\text{C}$
$T_j$	Maximum junction temperature		175	$^{\circ}\text{C}$
$dV/dt$	Critical rate of rise of reverse voltage		10000	V/ $\mu\text{s}$

**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	3	°C/W

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Parameter	Tests Conditions	Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = 45\text{ V}$		100	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$		7	15	mA
$V_F^{**}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 10\text{ A}$		0.63	V
		$T_j = 125^\circ\text{C}$	$I_F = 10\text{ A}$	0.5	0.57	
		$T_j = 25^\circ\text{C}$	$I_F = 20\text{ A}$		0.84	
		$T_j = 125^\circ\text{C}$	$I_F = 20\text{ A}$	0.65	0.72	

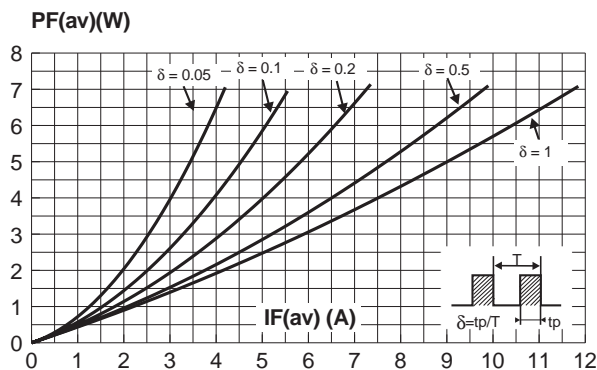
Pulse test : \*  $t_p = 380\text{ }\mu\text{s}$ ,  $\delta < 2\%$

\*\* $t_p = 5\text{ ms}$ ,  $\delta < 2\%$

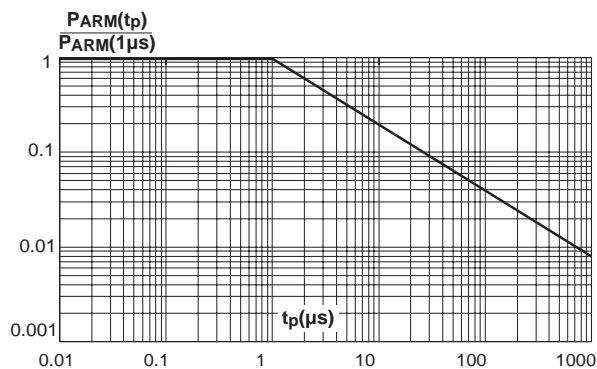
To evaluate the maximum conduction losses use the following equation :

$$P = 0.42 \times I_{F(AV)} + 0.015 I_{F(RMS)}^2$$

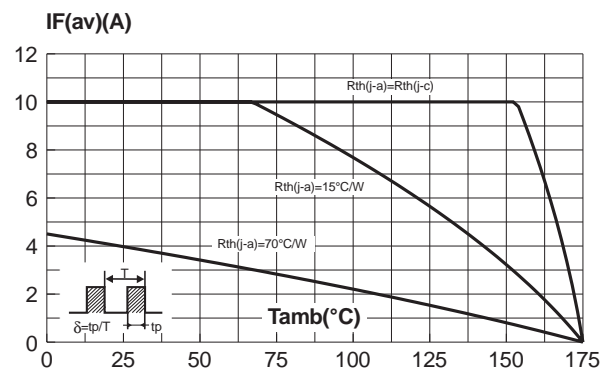
**Fig. 1:** Average forward power dissipation versus average forward current.



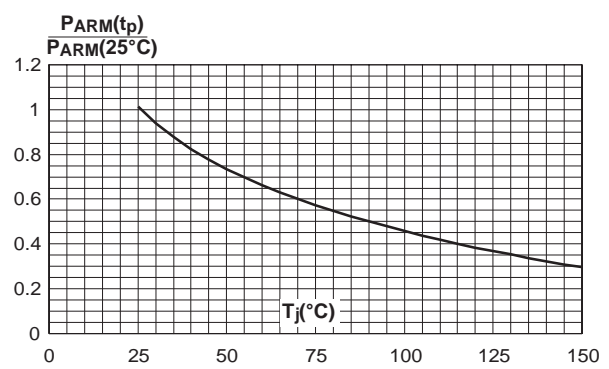
**Fig. 3:** Normalized avalanche power derating versus pulse duration.



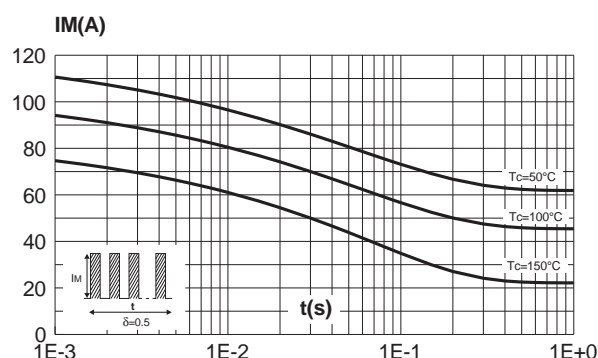
**Fig. 2:** Average forward current versus ambient temperature ( $\delta=0.5$ ).



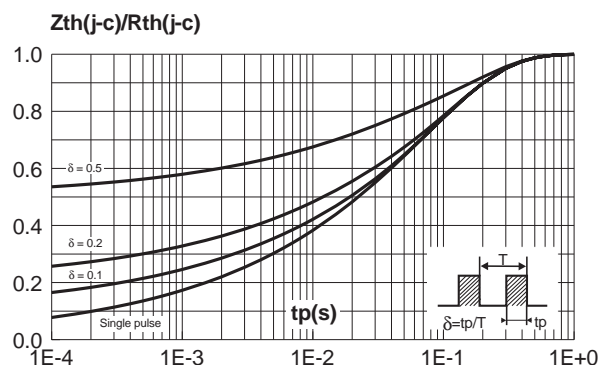
**Fig. 4:** Normalized avalanche power derating versus junction temperature.



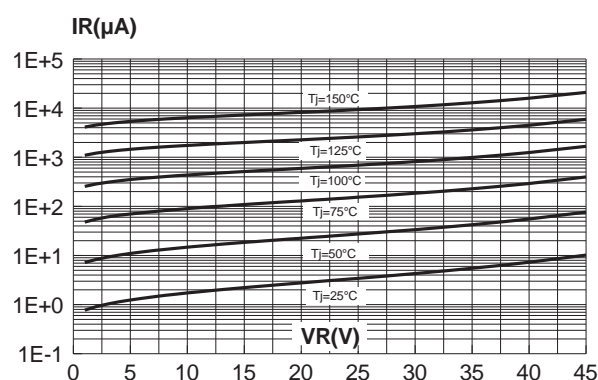
**Fig. 5:** Non repetitive surge peak forward current versus overload duration (maximum values).



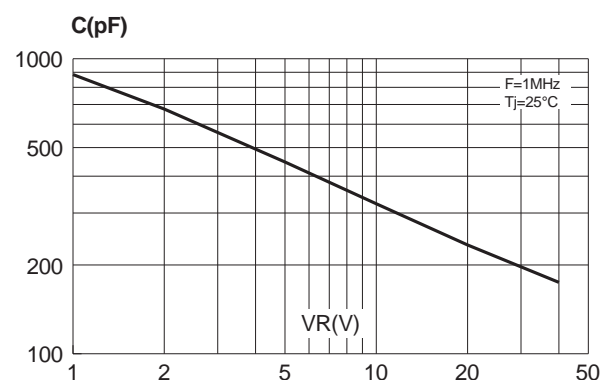
**Fig. 6:** Relative variation of thermal impedance junction to case versus pulse duration.



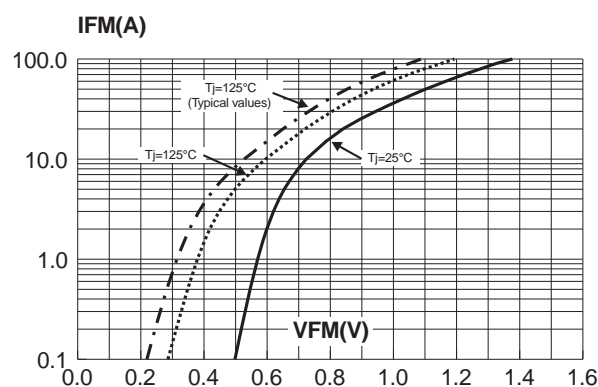
**Fig. 7:** Reverse leakage current versus reverse voltage applied (typical values).



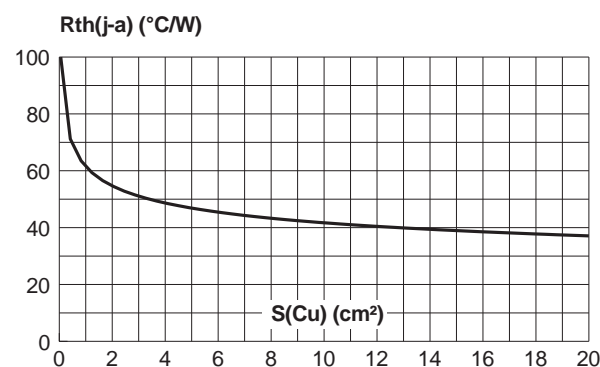
**Fig. 8:** Junction capacitance versus reverse voltage applied (typical values).



**Fig. 9:** Forward voltage drop versus forward current (maximum values).



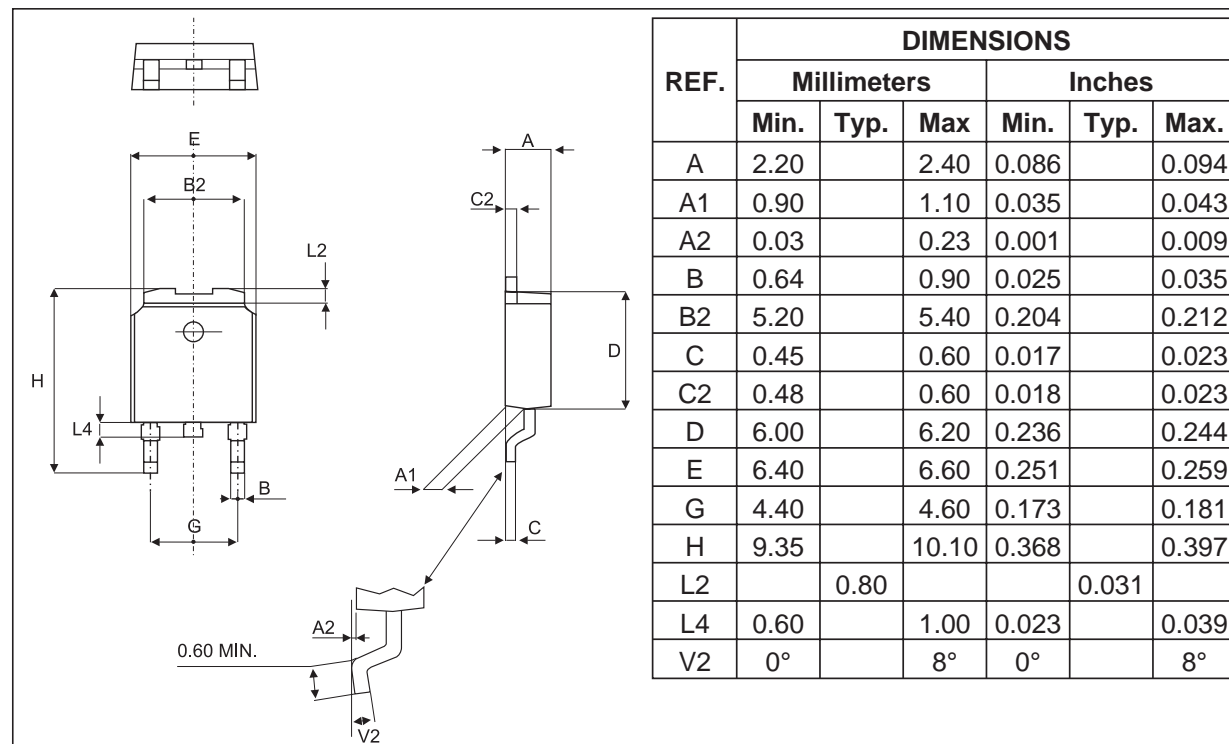
**Fig. 10:** Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board, copper thickness:  $35\mu\text{m}$ ) (STPS1045B).



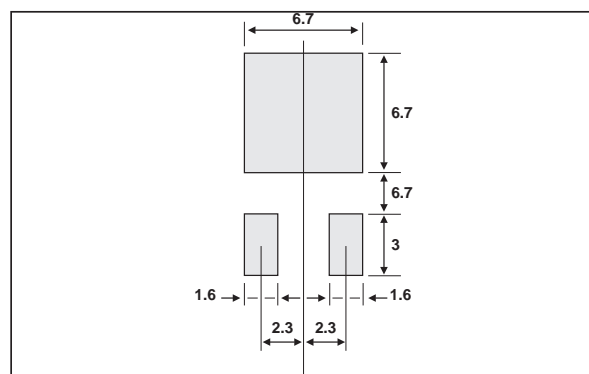
PACKAGE MECHANICAL DATA  
IPAK

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.035
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.035	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039
V1		10°			10°	

- COOLING METHOD: BY CONDUCTION (C)

**PACKAGE MECHANICAL DATA****DPAK**

• COOLING METHOD: BY CONDUCTION (C)

**FOOT PRINT DIMENSIONS (in millimeters)**

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